

GP1S196HCZ0F GP1S196HCZSF

Gap : 1.1mm, Slit : 0.3mm
Phototransistor Output,
Compact Transmissive
Photointerrupter



■ Description

GP1S196HCZ0F is a compact-package, photo-transistor output, transmissive photointerrupter, with opposing emitter and detector in a molding that provides non-contact sensing. The compact package series is a result of unique technology combining transfer and injection molding.

This device is half the size of the rest of the parts in this family.

■ Features

1. Transmissive with phototransistor output
2. Highlights :
 - Compact Size
 - Low Profile
 - Narrow Gap
 - Through-hole : **GP1S196HCZ0F**
 - SMT : **GP1S196HCZSF**
3. Key Parameters :
 - Gap Width : 1.1mm
 - Slit Width (detector side): 0.3mm
 - Package : 3.1×2×2.7mm
4. Lead free and RoHS directive compliant

■ Agency approvals/Compliance

1. Compliant with RoHS directive

■ Applications

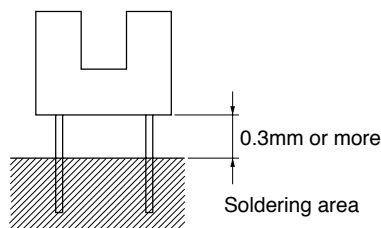
1. General purpose detection of object presence or motion.
2. Example : printer, lens control for camera

■ Absolute Maximum Ratings

(T_a=25°C)

Parameter		Symbol	Rating	Unit
Input	Forward current	I _F	30	mA
	Reverse voltage	V _R	6	V
	Power dissipation	P	75	mW
Output	Collector-emitter voltage	V _{CEO}	35	V
	Emitter-collector voltage	V _{ECO}	6	V
	Collector current	I _C	20	mA
	Collector power dissipation	P _C	75	mW
Total power dissipation		P _{tot}	100	mW
Operating temperature		T _{opr}	-25 to +85	°C
Storage temperature		T _{stg}	-40 to +100	°C
*1 Soldering temperature		T _{sol}	260	°C

*1 For 3s or less



(GP1S196HCZ0F)

■ Electro-optical Characteristics

(T_a=25°C)

Parameter			Symbol	Condition	MIN.	TYP.	MAX.	Unit
Input	Forward voltage		V _F	I _F =20mA	–	1.2	1.4	V
	Reverse current		I _R	V _R =3V	–	–	10	μA
Output	Collector dark current		I _{CEO}	V _{CE} =20V	–	–	100	nA
Transfer characteristics	Collector current		I _C	V _{CE} =5V, I _F =5mA	100	–	400	μA
	Collector-emitter saturation voltage		V _{CE(sat)}	I _F =10mA, I _C =40μA	–	–	0.4	V
	Response time	Rise time	t _r	V _{CE} =5V, I _C =100μA, R _L =1kΩ	–	50	150	μs
		Fall time	t _f		–	50	150	

Fig.1 Forward Current vs. Ambient Temperature

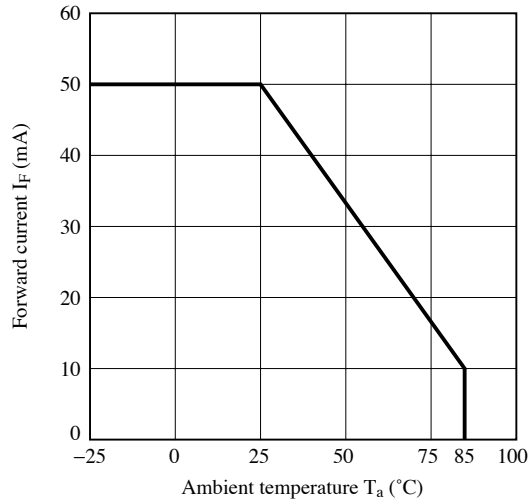


Fig.2 Power Dissipation vs. Ambient Temperature

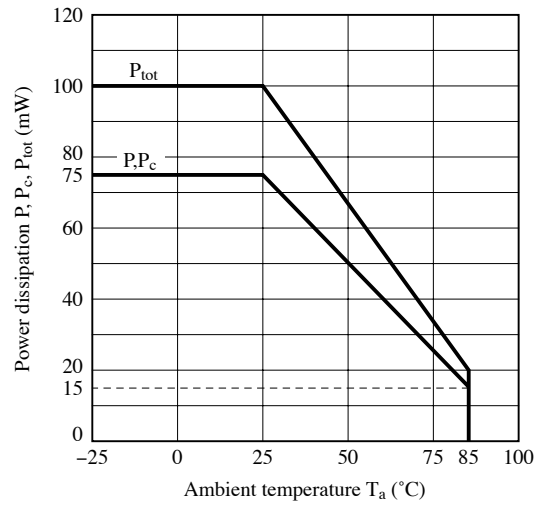


Fig.3 Forward Current vs. Forward Voltage

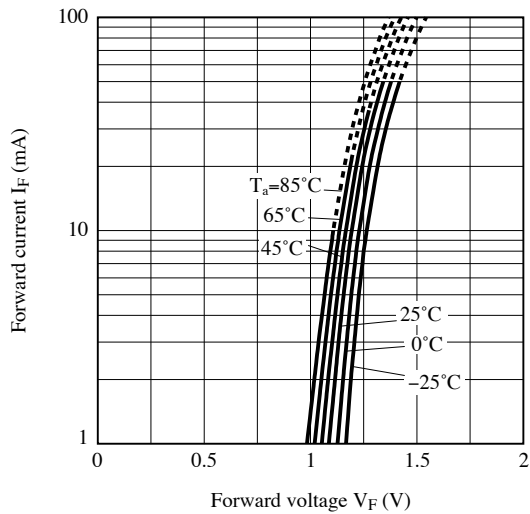


Fig.4 Collector Current vs. Forward Current

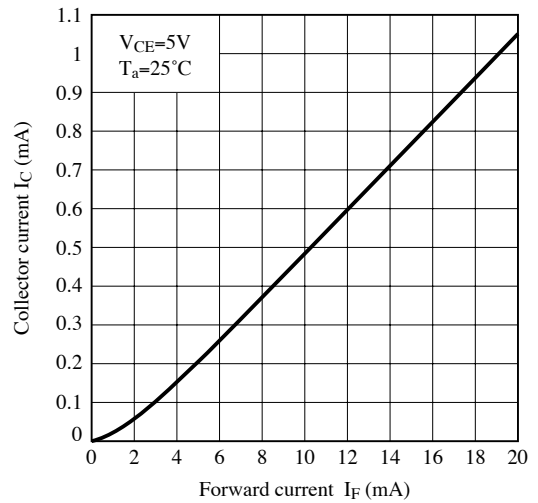


Fig.5 Collector Current vs. Collector-emitter Voltage

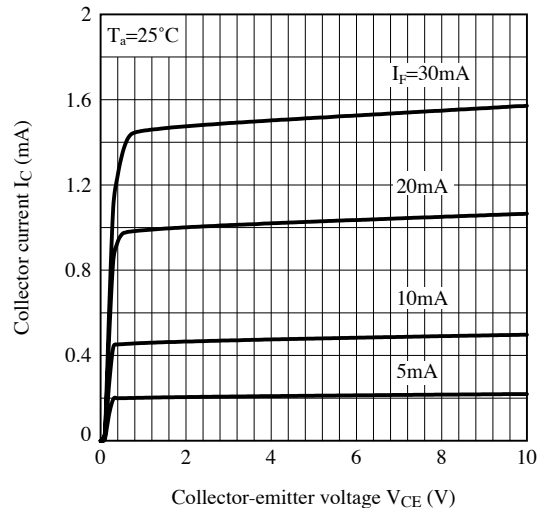


Fig.6 Relative Collector Current vs. Ambient Temperature

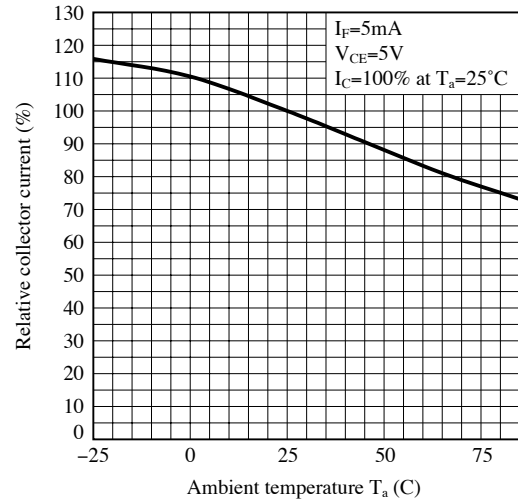


Fig.7 Collector-emitter Saturation Voltage vs. Ambient Temperature

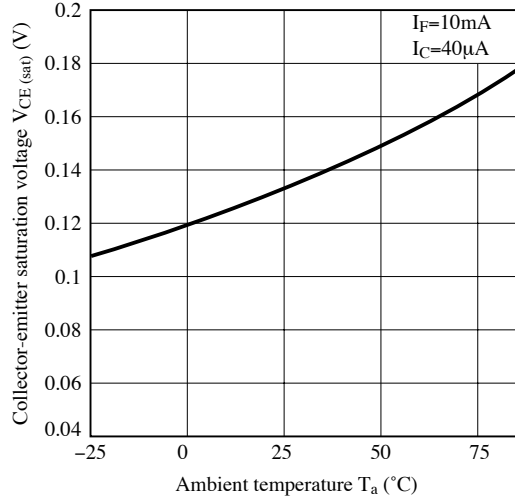


Fig.8 Collector Dark Current vs. Ambient Temperature

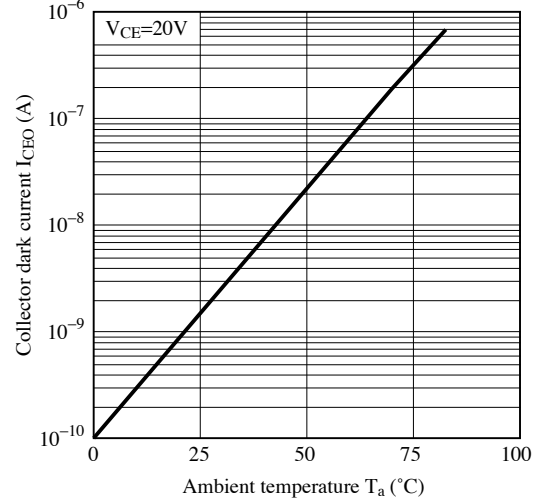


Fig.9 Response Time vs. Load Resistance

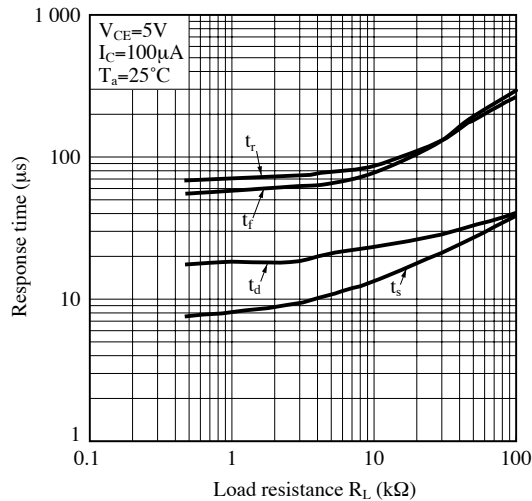


Fig.10 Test Circuit for Response Time

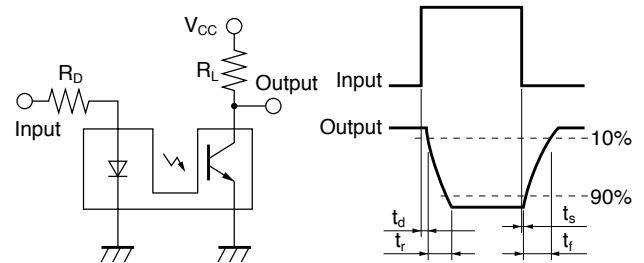


Fig.11 Relative Collector Current vs. Shield Distance (1)

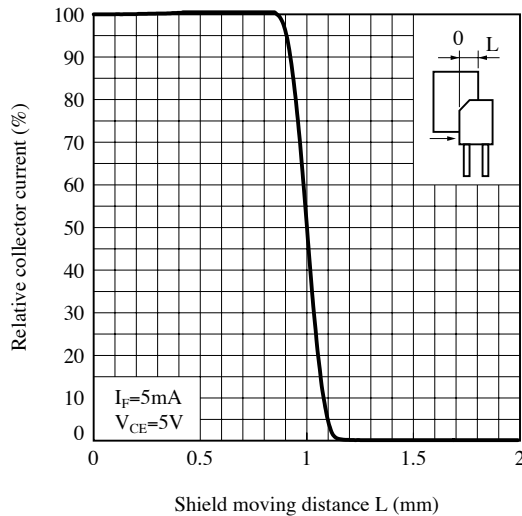
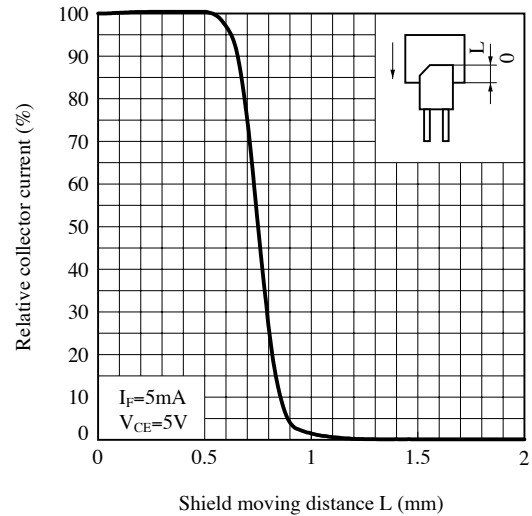


Fig.12 Relative Collector Current vs. Shield Distance (1)



Remarks : Please be aware that all data in the graph are just for reference and not for guarantee.

■ Design Considerations

● Design guide

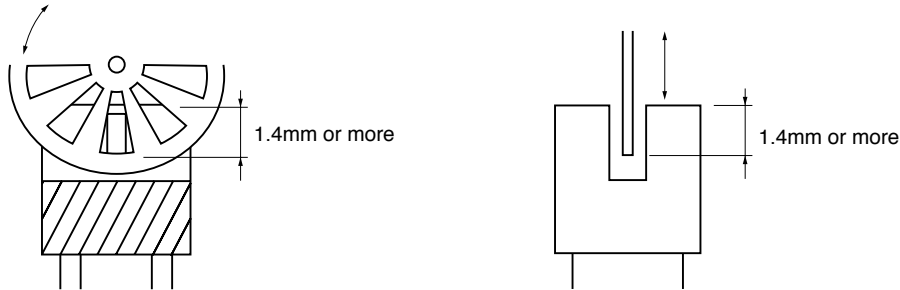
1) Prevention of detection error

To prevent photointerrupter from faulty operation caused by external light, do not set the detecting face to the external light.

2) Position of opaque board

Opaque board shall be installed at place 1.4mm or more from the top of elements.

(Example)



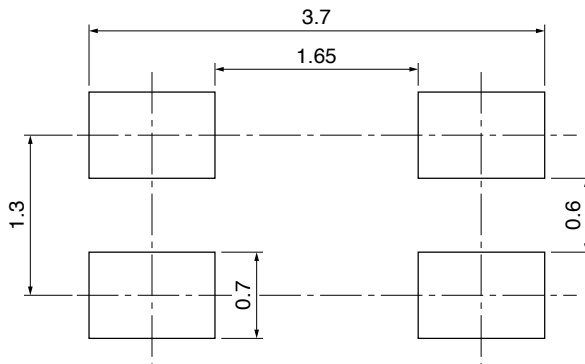
This product is not designed against irradiation and incorporates non-coherent IRED.

● Degradation

In general, the emission of the IRED used in photointerrupter will degrade over time.

In the case of long term operation, please take the general IRED degradation (50% degradation over 5 years) into the design consideration.

● Recommended Foot Print (Only for GP1S196HCZSF)



● Parts

This product is assembled using the below parts.

• Photodetector (qty. : 1)

Category	Material	Maximum Sensitivity wavelength (nm)	Sensitivity wavelength (nm)	Response time (μs)
Phototransistor	Silicon (Si)	930	700 to 1 200	20

• Photo emitter (qty. : 1)

Category	Material	Maximum light emitting wavelength (nm)	I/O Frequency (MHz)
Infrared emitting diode (non-coherent)	Gallium arsenide (GaAs)	950	0.3

• Material

Case	Lead frame	Lead frame plating
Black polyphernylene sulfide resin (UL94 V-0)	42Alloy	SnCu plating

■ Manufacturing Guidelines

● Storage and management after open (Only for GP1S196HCZSF)

Storage condition

Storage temp.: 5 to 30°C, Storage humidity : 70%RH or less at regular packaging.

Treatment after opening the moisture-proof package

After opening, you should mount the products while keeping them on the condition of 5 to 25°C and 70%RH or less in humidity within 4 days.

After opening the bag once even if the prolonged storage is necessary, you should mount the products within two weeks.

And when you store the rest of products you should put into a DRY BOX. Otherwise after the rest of products and silicagel are sealed up again, you should keep them under the condition of 5 to 30°C and 70%RH or less in humidity.

Baking before mounting

When the above-mentioned storage method could not be executed, please process the baking treatment before mounting the products.

However the baking treatment is permitted within one time.

Recommended condition : 125°C, 16 to 24 hours

*Do not process the baking treatment with the product wrapped. When the baking treatment processing, you should move the products to a metallic tray or fix temporarily the products to substrate.

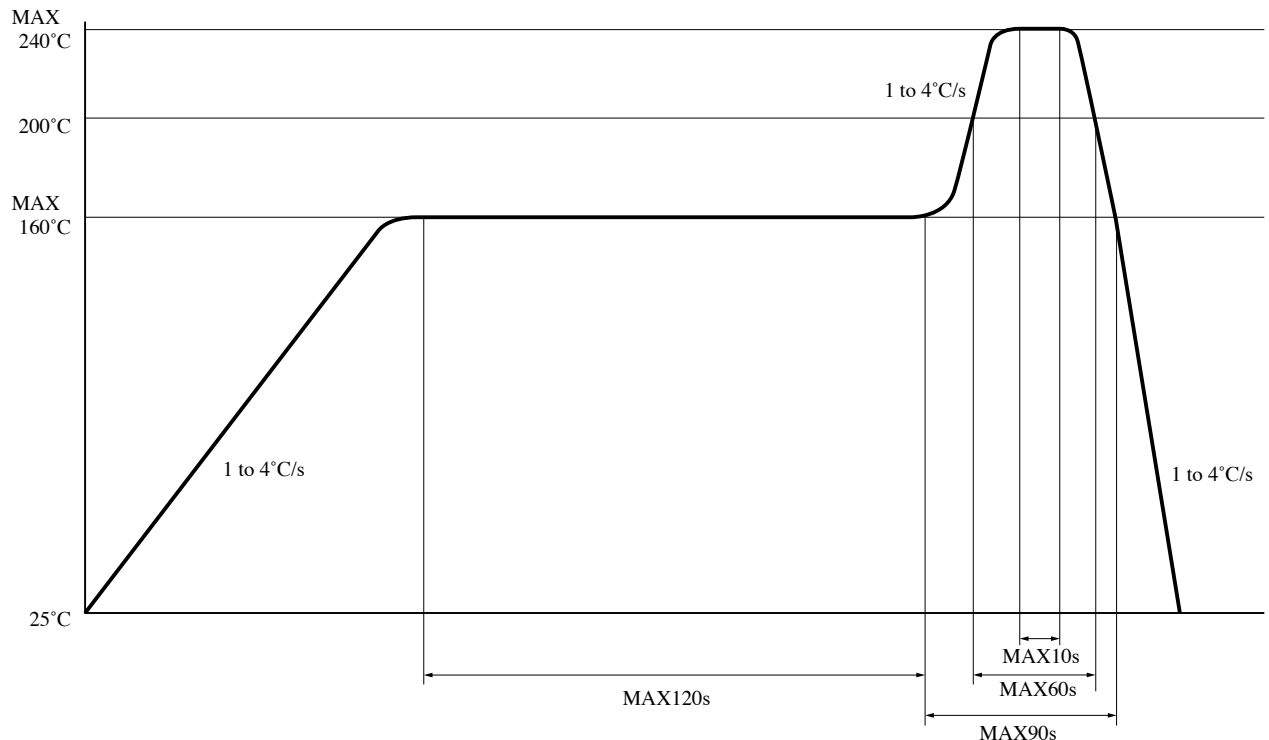
● Soldering Method

Reflow Soldering (Only for GP1S196HCZSF) :

Reflow soldering should follow the temperature profile shown below.

Soldering should not exceed the curve of temperature profile and time.

Please solder within one time.



Flow Soldering:

Soldering should be completed below 260°C and within 3 s.

Please solder within one time.

Soldering area is 0.3mm or more away from the bottom of housing.

Please take care not to let any external force exert on lead pins.

Please don't do soldering with preheating, and please don't do soldering by reflow.

Other notice

Please test the soldering method in actual condition and make sure the soldering works fine, since the impact on the junction between the device and PCB varies depending on the cooling and soldering conditions.

● Cleaning instructions**Solvent cleaning :**

Solvent temperature should be 45°C or below. Immersion time should be 3 minutes or less.

Ultrasonic cleaning :

Do not execute ultrasonic cleaning.

Recommended solvent materials :

Ethyl alcohol, Methyl alcohol and Isopropyl alcohol.

● Presence of ODC

This product shall not contain the following materials.

And they are not used in the production process for this product.

Regulation substances : CFCs, Halon, Carbon tetrachloride, 1.1.1-Trichloroethane (Methylchloroform)

Specific brominated flame retardants such as the PBBOs and PBBs are not used in this product at all.

This product shall not contain the following materials banned in the RoHS Directive (2002/95/EC).

- Lead, Mercury, Cadmium, Hexavalent chromium, Polybrominated biphenyls (PBB), Polybrominated diphenyl ethers (PBDE).

■ Package specification**● Sleeve package****1. Through-hole (GP1S196HCZ0F)****Package materials**

Sleeve : Polycarbonate

Stopper : Styrene-Elastomer

Package method

MAX. 200 pcs. of products shall be packaged in a sleeve. Both ends shall be closed by tabbed and tabless stoppers.

MAX. 50 sleeves in one case.

2. SMT Gullwing (GP1S196HCZSF)**Package materials**

Sleeve : Polycarbonate

Stopper : Styrene-Elastomer

Aluminium laminated Bag : Nylon, Polyphernylene, Aluminium

Package method

MAX. 200 pcs. of products shall be packaged in a sleeve. Both ends shall be closed by tabbed and tabless stoppers.

MAX. 50 sleeves with silicagel are enclosed in aluminium laminated bag. After sealing up the bag, it encased in one case.

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